



PRODUCT NAME : 2SB810 PNP General Purpose Transistor

PRICE : Rs 20.00

SKU : RM2146



NOTE: THE PRODUCT MAY BE DIFFERENT FROM IMAGE SHOWN. Copyrights by Robomart.com

DESCRIPTION

Features

- Collector-Emitter Volt (V_{ce0}): 30V
- Collector-Base Volt (V_{cb0}): 25V
- Collector Current (I_c): 0.7A
- h_{fe} : 110-400 @ 100mA
- Power Dissipation (P_{tot}): 350mW
- Current-Gain-Bandwidth (f_{total}): 160MHz
- Type: PNP

NEC

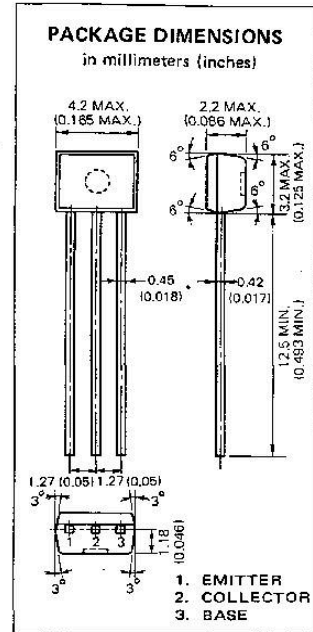
PNP SILICON TRANSISTOR 2SB810

DESCRIPTION The 2SB810 is designed for use in output stage of portable radio and cassette type tape recorder, general purpose applications.

- FEATURES**
- High total power dissipation.
 $P_T = 350$ mW
 - High h_{FE} and low $V_{CE(sat)}$.
 $h_{FE}(I_C = -100$ mA) : 200 TYP.
 $V_{CE(sat)}(-700$ mA) : -0.25 V TYP.
 - Complementary to the NEC 2SD1020 NPN transistor.

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures	
Storage Temperature -55 to $+150$ °C
Junction Temperature $+150$ °C Maximum
Maximum Power Dissipation ($T_a = 25$ °C)	
Total Power Dissipation 350 mW
Maximum Voltages and Currents ($T_a = 25$ °C)	
V_{CBO} Collector to Base Voltage -30 V
V_{CEO} Collector to Emitter Voltage -25 V
V_{EBO} Emitter to Base Voltage -5.0 V
I_C Collector Current -700 mA
I_B Base Current -150 mA



ELECTRICAL CHARACTERISTICS ($T_a = 25$ °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
h_{FE1}^*	DC Current Gain	110	200	400	—	$V_{CE} = -1.0$ V, $I_C = -100$ mA
h_{FE2}^*	DC Current Gain	50	100	—	—	$V_{CE} = -1.0$ V, $I_C = -700$ mA
C_{ob}	Collector to Base Capacitance	—	17	40	pF	$V_{CB} = -6.0$ V, $I_E = 0$, $f = 1.0$ MHz
f_T	Gain Bandwidth Product	50	160	—	MHz	$V_{CE} = -6.0$ V, $I_E = -10$ mA
V_{BE}^*	Base to Emitter Voltage	-600	-640	-700	mV	$V_{CE} = -6.0$ V, $I_C = -10$ mA
$V_{CE(sat)}^*$	Collector Saturation Voltage	—	-0.25	-0.4	V	$I_C = -700$ mA, $I_B = -70$ mA
$V_{BE(sat)}^*$	Base Saturation Voltage	—	-0.95	-1.2	V	$I_C = -700$ mA, $I_B = -70$ mA
I_{CBO}	Collector Cutoff Current	—	-100	-100	nA	$V_{CB} = -30$ V, $I_E = 0$
I_{EBO}	Emitter Cutoff Current	—	-100	-100	nA	$V_{EB} = -5.0$ V, $I_C = 0$

* Pulsed PW ≤ 350 μ s, duty cycle ≤ 2.0 %

Classification of h_{FE1}

Rank	M	J	H	F	E
Range	110 - 180	135 - 220	170 - 270	200 - 320	250 - 400

h_{FE1} Test Conditions : $V_{CE} = -1.0$ V, $I_C = -100$ mA

